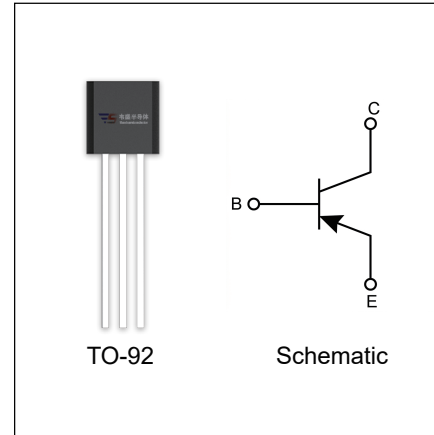


2SA562 TRANSISTOR (PNP)

FEATURES

- Excellent h_{FE} Linearity



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-500	mA
P_C	Collector Power Dissipation	500	mW
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

T_a=25 °C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR) _{CBO}	I _C =-100μA, I _E =0	-35			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _C =-1mA, I _B =0	-30			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-35V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-1V, I _C =-100mA	70		240	
Collector-emitter saturation voltage	V _{CE(SAT)}	I _C =-100mA, I _B =-10mA			-0.25	V
Base-emitter voltage	V _{BE}	V _{CE} =-1V, I _C =-100mA			-1	V
Transition frequency	f _T	V _{CE} =-6V, I _C =-20mA		200		MHz
Collector output capacitance	C _{ob}	V _{CE} =-6V, I _E =0, f=1MHz	13			pF

CLASSIFICATION OF h_{FE}

RANK	O	Y
RANGE	70-140	120-240

Static Characteristic
